TOSHIBA TA4011FU

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA4011FU

UHF WIDE BAND AMPLIFIER APPLICATIONS

FEATURES

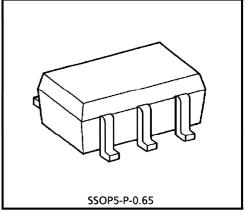
Low Current $: I_{CC} = 3.5 \, \text{mA}$

Wide Band : $f = 2.4 \, \text{GHz} \, (3 \, \text{dB down})$

Operating Supply Voltage : V_{CC} = 1.5~3 V

MAXIMUM RATINGS (Ta = 25°C)

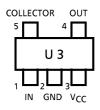
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage 1	V _{CC1}	3.2	V
Supply Voltage 2 (Note 1)	V _{CC2}	4	V
Total Power Dissipation (Note 2)	PD	300	mW
Operating Temperature	T _{opr}	- 40∼85	°C
Storage Temperature	T _{stg}	- 55∼150	°C



Weight: 0.006 g (Typ.)

(Note 1): When V_{CC} is operated at less than 1/4 duty cycle. (Note 2): When mounted on the glass epoxy of $2.5 \text{ cm}^2 \times 1.6 \text{ t}$

PIN ASSIGNMENT



CAUTION

This device electrostatic sensitivity. Please handle with caution.

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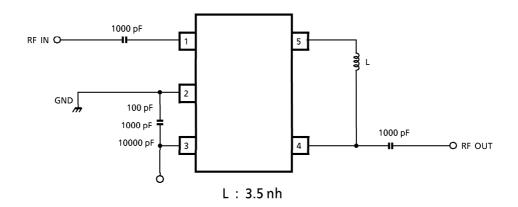
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ELECTRICAL CHARACTERISTICS (Ta = 25°C, Zg = ZI = 50 Ω)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Circuit Current	lcc	V _{CC} = 2 V, Non carrier	2.5	3.5	4.5	mA
Band Width	BW	V _{CC} = 2 V (Note 3)	2.2	2.4	_	GHz
Insertion Gain	S21 ²	V _{CC} = 2 V, f = 1.5 GHz	8	10	_	dB
Noise Figure	NF	V _{CC} = 2 V, f = 1.5 GHz	_	6.5	8	dB
Isolation	S12 ²	V _{CC} = 2 V, f = 1.5 GHz	_	- 22	_	dB
Input Return Loss	S11 ²	V _{CC} = 2 V, f = 1.5 GHz	_	- 6.5	_	dB
Output Return Loss	S22 ²	V _{CC} = 2 V, f = 1.5 GHz	_	- 5.5	_	dB
Output Power at 1 dB Gain Compression	Po1dB	V _{CC} = 2 V, f = 1.5 GHz	_	- 6		dBmW

(Note 3) : BW is the frequency of 3 dB down from $|S21|^2$ at 1.5 GHz.

RF TEST CIRCUIT (TOP VIEW)



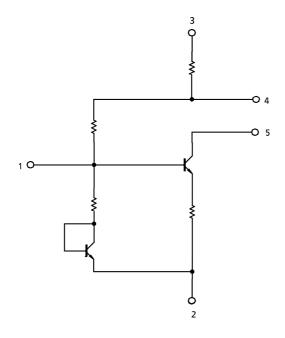
NOTICE

The circuits and measurements contained in this document are given only in the context of as examples of applications for these products.

Moreover, these example application circuits are not intended for mass production, since the high-frequency characteristics (the AC characteristics) of these devices will be affected by the external components which the customer uses, by the design of the circuit and by various other conditions. It is the responsibility of the customer to design external circuits which correctly implement the intended application, and to check the characteristics of the design.

TOSHIBA assume no responsibility for the integrity of customer circuit designs or applications.

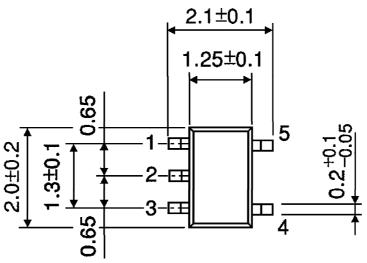
EQUIVALENT CIRCUIT

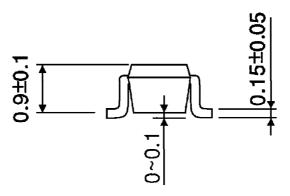


Unit: mm

PACKAGE DIMENSIONS

SSOP5-P-0.65





Weight: 0.006 g (Typ.)